# LM611 Operational Amplifier and Adjustable Reference

**Check for Samples: LM611**

## FEATURES

- **OP AMP**
- **Low operating current: 300 μA (op amp)**
- **Wide supply voltage range: 4V to 36V**
- **Wide common-mode range: $V^-$ to ($V^+$−1.8V)**
- **Wide differential input voltage: ±36V**
- **Available in low cost 8-pin DIP**
- **Available in plastic package rated for Military Temperature Range Operation**
- **REFERENCE**
- **Adjustable output voltage: 1.2V to 6.3V**
- **Tight initial tolerance available: ±0.6%**
- **Wide operating current range: 17 μA to 20 mA**
- **Reference floats above ground**
- **Tolerant of load capacitance**

## APPLICATIONS

- **Transducer bridge driver**
- **Process and Mass Flow Control systems**
- **Power supply voltage monitor**
- **Buffered voltage references for A/D's**

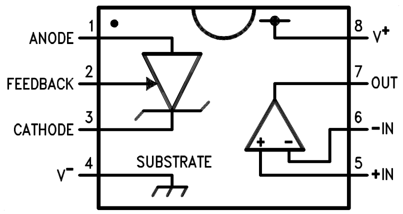
## DESCRIPTION

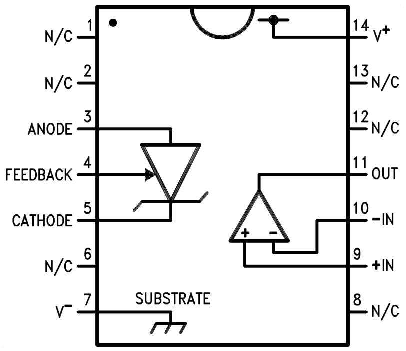
The LM611 consists of a single-supply op-amp and a programmable voltage reference in one space saving 8-pin package. The op-amp out-performs most single-supply op-amps by providing higher speed and bandwidth along with low supply current. This device was specifically designed to lower cost and board space requirements in transducer, test, measurement and data acquisition systems.

Combining a stable voltage reference with a wide output swing op-amp makes the LM611 ideal for single supply transducers, signal conditioning and bridge driving where large common-mode signals are common. The voltage reference consists of a reliable band-gap design that maintains low dynamic output impedance (1Ω typical), excellent initial tolerance (0.6%), and the ability to be programmed from 1.2V to 6.3V via two external resistors. The voltage reference is very stable even when driving large capacitive loads, as are commonly encountered in CMOS data acquisition systems.

As a member of National's Super-Block™ family, the LM611 is a space-saving monolithic alternative to a multi-chip solution, offering a high level of integration without sacrificing performance.

### Connection Diagram





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## Absolute Maximum Ratings [1]

| | |
|---|---|
| Voltage on Any Pins Except $V_R$ | |
| (referred to $V^-$ pin) | 36V (Max) |
| [2] | −0.3V (Min) |
| Current through Any Input Pin and | |
| $V_R$ Pin | ±20 mA |
| Differential Input Voltage | |
| Military and Industrial | ±36V |
| Commercial | ±32V |
| Storage Temperature Range | $-65°C \leq T_J \leq +150°C$ |
| Maximum Junction Temperature | 150°C |
| Thermal Resistance, Junction-to-Ambient [3] | |
| N Package | 100°C/W |
| M Package | 150°C/W |
| Soldering Information Soldering (10 seconds) | |
| N Package | 260°C |
| M Package | 220°C |
| ESD Tolerance [4] | ±1 kV |

(1) Absolute maximum ratings indicate limits beyond which damage to the component may occur. Electrical specifications do not apply when operating the device beyond its rated operating conditions.

(2) More accurately, it is excessive current flow, with resulting excess heating, that limits the voltages on all pins. When any pin is pulled a diode drop below $V^-$, a parasitic NPN transistor turns ON. No latch-up will occur as long as the current through that pin remains below the Maximum Rating. Operation is undefined and unpredictable when any parasitic diode or transistor is conducting.

(3) Junction temperature may be calculated using $T_J = T_A + P_D\ \theta_{JA}$. The given thermal resistance is worst-case for packages in sockets in still air. For packages soldered to copper-clad board with dissipation from one op amp or reference output transistor, nominal $\theta_{JA}$ is 90°C/W for the N package and 135°C/W for the M package.

(4) Human body model, 100 pF discharged through a 1.5 kΩ resistor.

## Operating Temperature Range

| | |
|---|---|
| LM611AI, LM611I, LM611BI | $-40°C \leq T_J \leq +85°C$ |
| LM611AM, LM611M | $-55°C \leq T_J \leq +125°C$ |
| LM611C | $0°C \leq T_J \leq 70°C$ |

## Electrical Characteristics

These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\ \mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25°C$; limits in **boldface type** apply over the **Operating Temperature Range.**

| Symbol | Parameter | Conditions | Typical (1) | LM611AM LM611AI Limits (2) | LM611M LM611BI LM611I LM611C Limits (2) | Units |
|---|---|---|---|---|---|---|
| $I_S$ | Total Supply Current | $R_{LOAD} = \infty$, | 210 | 300 | 350 | μA max |
| | | $4V \le V^+ \le 36V$ (32V for LM611C) | **221** | **320** | **370** | μA max |
| $V_S$ | Supply Voltage Range | | 2.2 | 2.8 | 2.8 | V min |
| | | | **2.9** | **3** | **3** | V min |
| | | | 46 | 36 | 32 | V max |
| | | | **43** | **36** | **32** | V max |
| **OPERATIONAL AMPLIFIER** | | | | | | |
| $V_{OS1}$ | $V_{OS}$ Over Supply | $4V \le V^+ \le 36V$ | 1.5 | 3.5 | 5.0 | mV max |
| | | ($4V \le V^+ \le 32V$ for LM611C) | **2.0** | **6.0** | **7.0** | mV max |
| $V_{OS2}$ | $V_{OS}$ Over $V_{CM}$ | $V_{CM}$ = 0V through $V_{CM}$ = | 1.0 | 3.5 | 5.0 | mV max |
| | | $(V^+ - 1.8V)$, $V^+ = 30V$, $V^- = 0V$ | **1.5** | **6.0** | **7.0** | mV max |
| $\frac{V_{OS3}}{\Delta T}$ | Average $V_{OS}$ Drift | (2) | **15** | | | μV/°C |
| | | | | | | max |
| $I_B$ | Input Bias Current | | 10 | 25 | 35 | nA max |
| | | | **11** | **30** | **40** | nA max |
| $I_{OS}$ | Input Offset Current | | 0.2 | 4 | 4 | nA max |
| | | | **0.3** | **5** | **5** | nA max |
| $\frac{I_{OS1}}{\Delta T}$ | Average Offset Drift Current | | **4** | | | pA/°C |
| $R_{IN}$ | Input Resistance | Differential | 1800 | | | MΩ |
| | | Common-Mode | 3800 | | | MΩ |
| $C_{IN}$ | Input Capacitance | Common-Mode | 5.7 | | | pF |
| $e_n$ | Voltage Noise | f = 100 Hz, Input Referred | 74 | | | $nV/\sqrt{Hz}$ |
| $I_n$ | Current Noise | f = 100 Hz, Input Referred | 58 | | | $fA/\sqrt{Hz}$ |
| CMRR | Common-Mode | $V^+ = 30V$, $0V \le V_{CM} \le (V^+ - 1.8V)$ | 95 | 80 | 75 | dB min |
| | Rejection-Ratio | $CMRR = 20 \log (\Delta V_{CM}/\Delta V_{OS})$ | **90** | **75** | **70** | dB min |
| PSRR | Power Supply | $4V \le V^+ \le 30V$, $V_{CM} = V^+/2$, | 110 | 80 | 75 | dB min |
| | Rejection-Ratio | $PSRR = 20 \log (\Delta V^+/\Delta V_{OS})$ | **100** | **75** | **70** | dB min |
| $A_V$ | Open Loop | $R_L = 10\ k\Omega$ to GND, $V^+ = 30V$, | 500 | 100 | 94 | V/mV |
| | Voltage Gain | $5V \le V_{OUT} \le 25V$ | **50** | **40** | **40** | min |
| SR | Slew Rate | $V^+ = 30V$ (3) | 0.70 | 0.55 | 0.50 | V/μs |
| | | | **0.65** | **0.45** | **0.45** | |
| GBW | Gain Bandwidth | $C_L = 50\ pF$ | 0.80 | | | MHz |

(1) Typical values in standard typeface are for $T_J = 25°C$; values in **boldface type** apply for the full operating temperature range. These values represent the most likely parametric norm.
(2) All limits are guaranteed at room temperature (standard type face) or at operating temperature extremes **(bold face type)**.
(3) Slew rate is measured with op amp in a voltage follower configuration. For rising slew rate, the input voltage is driven from 5V to 25V, and the output voltage transition is sampled at 10V and 20V. For falling slew rate, the input voltage is driven from 25V to 5V, and output voltage transition is sampled at 20V and 10V.

## Electrical Characteristics (continued)

These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\ \mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25°C$; limits in **boldface type** apply over the **Operating Temperature Range.**

| | | | | | **LM611M** | |
|---|---|---|---|---|---|---|
| | | | | **LM611AM** | **LM611BI** | |
| **Symbol** | **Parameter** | **Conditions** | **Typical** | **LM611AI** | **LM611I** | **Units** |
| | | | (1) | **Limits** | **LM611C** | |
| | | | | (2) | **Limits** | |
| | | | | | (2) | |
| | | | **0.50** | | | |
| $V_{O1}$ | Output Voltage | $R_L = 10\ k\Omega$ to GND | $V^+ - 1.4$ | $V^+ - 1.7$ | $V^+ - 1.8$ | V min |
| | Swing High | $V^+ = 36V$ (32V for LM611C) | **$V^+ - 1.6$** | **$V^+ - 1.9$** | **$V^+ - 1.9$** | V min |
| $V_{O2}$ | Output Voltage | $R_L = 10\ k\Omega$ to $V^+$ | $V^- + 0.8$ | $V^- + 0.9$ | $V^- + 0.95$ | V max |
| | Swing Low | $V^+ = 36V$ (32V for LM611C) | **$V^- + 0.9$** | **$V^- + 1.0$** | **$V^- + 1.0$** | V max |
| $I_{OUT}$ | Output Source | $V_{OUT} = 2.5V$, $V_{+IN} = 0V$, | 25 | 20 | 16 | mA min |
| | Current | $V_{-IN} = -0.3V$ | **15** | **13** | **13** | mA min |
| $I_{SINK}$ | Output Sink | $V_{OUT} = 1.6V$, $V_{+IN} = 0V$, | 17 | 14 | 13 | mA min |
| | Current | $V_{-IN} = 0.3V$ | **9** | **8** | **8** | mA min |
| $I_{SHORT}$ | Short Circuit Current | $V_{OUT} = 0V$, $V_{+IN} = 3V$, | 30 | 50 | 50 | mA max |
| | | $V_{-IN} = 2V$, Source | **40** | **60** | **60** | mA max |
| | | $V_{OUT} = 5V$, $V_{+IN} = 2V$, | 30 | 60 | 70 | mA max |
| | | $V_{-IN} = 3V$, Sink | **32** | **80** | **90** | mA max |
| **VOLTAGE REFERENCE** | | | | | | |
| $V_R$ | Reference Voltage | (4) | 1.244 | 1.2365 | 1.2191 | V min |
| | | | | 1.2515 | 1.2689 | V max |
| | | | | (±0.6%) | (±2.0%) | |
| $\frac{\Delta V_R}{\Delta T_J}$ | Average Temperature Drift | (5) | **10** | **80** | **150** | PPM/°C max |
| $\frac{\Delta V_R}{\Delta T_J}$ | Hysteresis | $Hyst = (Vro' - Vro)/\Delta T_J$ (6) | **3.2** | | | µV/°C |
| $\frac{\Delta V_R}{\Delta I_R}$ | $V_R$ Change | $V_{R(100\ \mu A)} - V_{R(17\ \mu A)}$ | 0.05 | 1 | 1 | mV max |
| | with Current | | **0.1** | **1.1** | **1.1** | mV max |
| | | $V_{R(10\ mA)} - V_{R(100\ \mu A)}$ | 1.5 | 5 | 5 | mV max |
| | | (7) | **2.0** | **5.5** | **5.5** | mV max |
| R | Resistance | $\Delta V_{R(10 \to 0.1\ mA)}/9.9\ mA$ | **0.2** | **0.56** | **0.56** | Ω max |
| | | $\Delta V_{R(100 \to 17\ \mu A)}/83\ \mu A$ | **0.6** | **13** | **13** | Ω max |
| $\frac{\Delta V_R}{V_{RO}}$ | $V_R$ Change with | $V_{R(Vro\ =\ Vr)} - V_{R(Vro\ =\ 6.3V)}$ | 2.5 | 7 | 7 | mV max |
| | High $V_{RO}$ | (5.06V between Anode and FEEDBACK) | **2.8** | **10** | **10** | mV max |

(4) $V_R$ is the cathode-feedback voltage, nominally 1.244V.

(5) Average reference drift is calculated from the measurement of the reference voltage at 25°C and at the temperature extremes. The drift, in ppm/°C, is $10^6 \bullet \Delta V_R/(V_{R[25°C]} \bullet \Delta T_J)$, where $\Delta V_R$ is the lowest value subtracted from the highest, $V_{R[25°C]}$ is the value at 25°C, and $\Delta T_J$ is the temperature range. This parameter is guaranteed by design and sample testing.

(6) Hysteresis is the change in $V_R$ caused by a change in $T_J$, after the reference has been "dehysterized". To dehysterize the reference; that is minimize the hysteresis to the typical value, its junction temperature should be cycled in the following pattern, spiraling in toward 25°C: 25°C, 85°C, −40°C, 70°C, 0°C, 25°C.

(7) Low contact resistance is required for accurate measurement.

## Electrical Characteristics (continued)

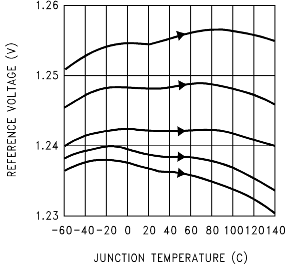
These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\ \mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25°C$; limits in **boldface type** apply over the **Operating Temperature Range.**

| Symbol | Parameter | Conditions | Typical[1] | LM611AM LM611AI Limits[2] | LM611M LM611BI LM611I LM611C Limits[2] | Units |
|---|---|---|---|---|---|---|
| $\frac{\Delta V_R}{\Delta V^+}$ | $V_R$ Change with | $V_{R(V+ = 5V)} - V_{R(V+ = 36V)}$ | 0.1 | 1.2 | 1.2 | mV max |
| | $V^+$ Change | ($V^+$ = 32V for LM611C) | **0.1** | **1.3** | **1.3** | mV max |
| | | $V_{R(V+ = 5V)} - V_{R(V+ = 3V)}$ | 0.01 | 1 | 1 | mV max |
| | | | **0.01** | **1.5** | **1.5** | mV max |
| $\frac{\Delta V_R}{\Delta V_{ANODE}}$ | $V_R$ Change with | $V^+ = V^+$ max, $\Delta V_R = V_R$ | | | | |
| | $V_{ANODE}$ Change | (@ $V_{ANODE} = V^- =$ GND) − $V_R$ | 0.7 | 1.5 | 1.6 | mV max |
| | | (@ $V_{ANODE} = V^+ - 1.0V$) | **3.3** | **3.0** | **3.0** | mV max |
| $I_{FB}$ | FEEDBACK Bias | $I_{FB}$; $V_{ANODE} \le V_{FB} \le 5.06V$ | 22 | 35 | 50 | nA max |
| | Current | | **29** | **40** | **55** | nA max |
| $e_n$ | $V_R$ Noise | 10 Hz to 10,000 Hz, $V_{RO} = V_R$ | 30 | | | $\mu V_{RMS}$ |

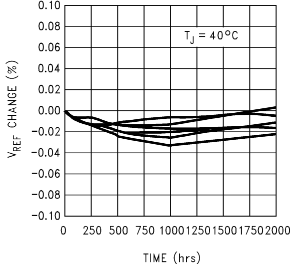
## Typical Performance Characteristics (Reference)

$T_J$ = 25°C, FEEDBACK pin shorted to $V^-$ = 0V, unless otherwise noted

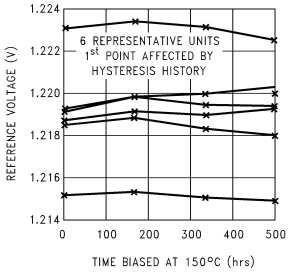
**Reference Voltage vs Temp on 5 Representative Units**



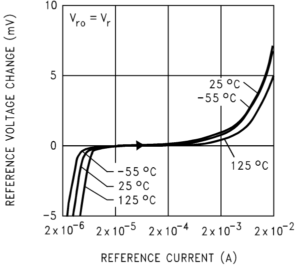
**Reference Voltage Drift**



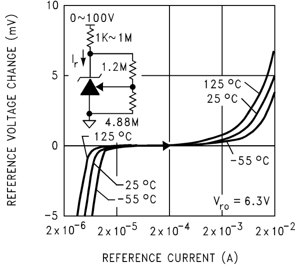
**Accelerated Reference Voltage Drift vs Time**



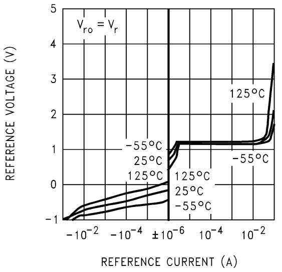
**Reference Voltage vs Current and Temperature**



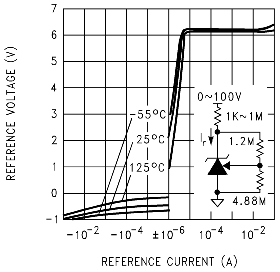
**Reference Voltage vs Current and Temperature**



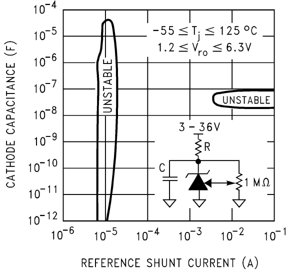
**Reference Voltage vs Reference Current**



**Reference Voltage vs Reference Current**



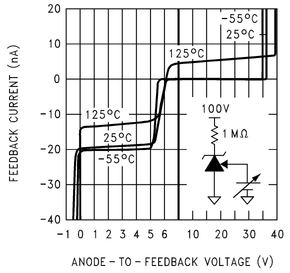
**Reference AC Stability Range**



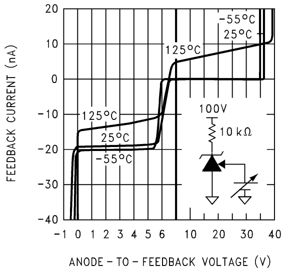
## Typical Performance Characteristics (Reference) (continued)

$T_J$ = 25°C, FEEDBACK pin shorted to $V^-$ = 0V, unless otherwise noted

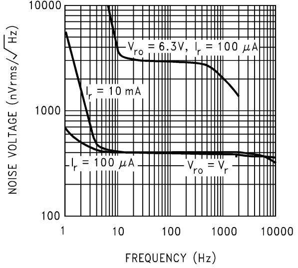
**Feedback Current vs Feedback-to-Anode Voltage**



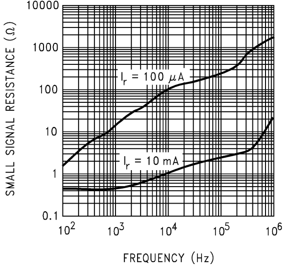
**Feedback Current vs Feedback-to-Anode Voltage**



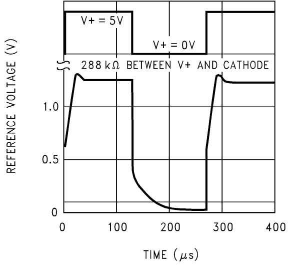
**Reference Noise Voltage vs Frequency**



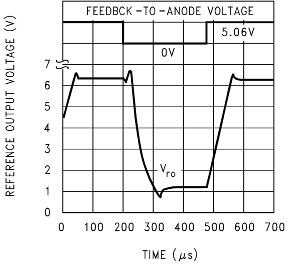
**Reference Small-Signal Resistance vs Frequency**



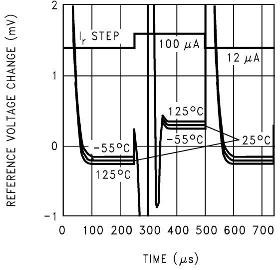
**Reference Power-Up Time**



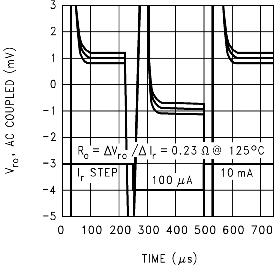
**Reference Voltage with Feedback Voltage Step**



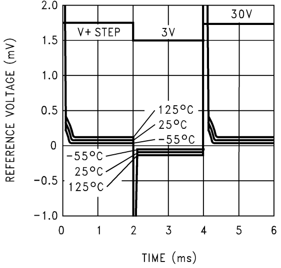
**Reference Voltage with 100~12 μA Current Step**



**Reference Step Response for 100 μA ~ 10 mA Current Step**



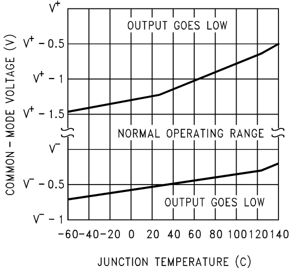
**Reference Voltage Change with Supply Voltage Step**



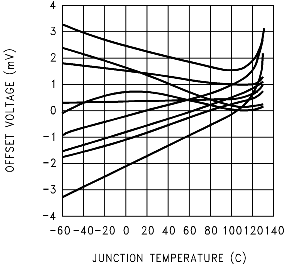
## Typical Performance Characteristics (Op Amps)

$V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25°C$, unless otherwise noted

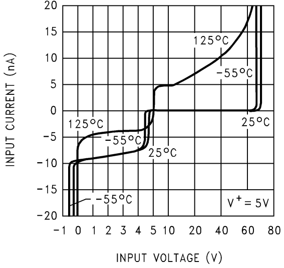
**Input Common-Mode Voltage Range vs Temperature**



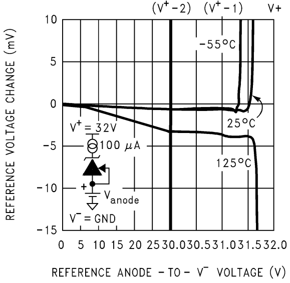
**$V_{OS}$ vs Junction Temperature**



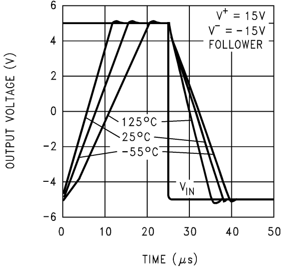
**Input Bias Current vs Common-Mode Voltage**



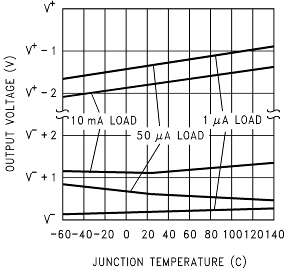
**Reference Change vs Common-Mode Voltage**



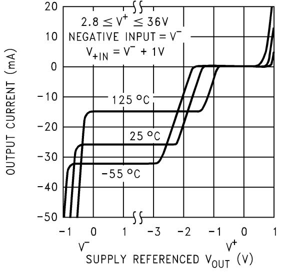
**Large-Signal Step Response**



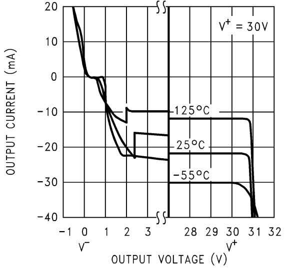
**Output Voltage Swing vs Temp. and Current**



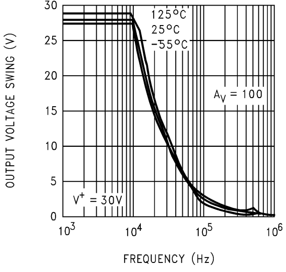
**Output Source Current vs Output Voltage and Temp.**



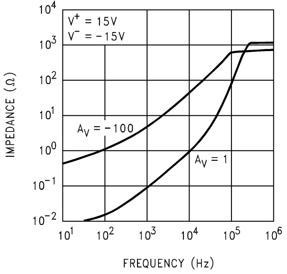
**Output Sink Current vs Output Voltage**



**Output Swing, Large Signal**



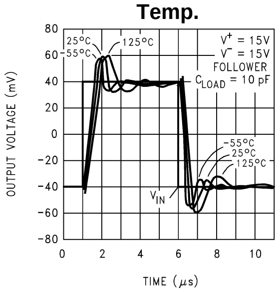
**Output Impedance vs Frequency and Gain**



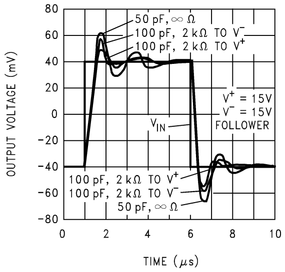
## Typical Performance Characteristics (Op Amps) (continued)

$V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25°C$, unless otherwise noted

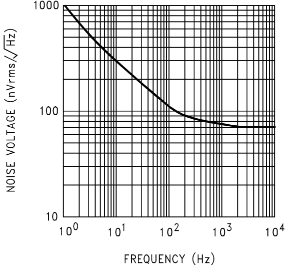
### Small Signal Pulse Response vs Temp.



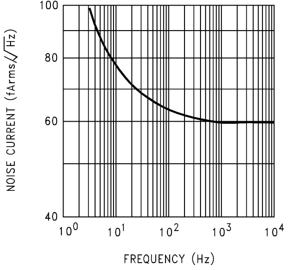
### Small-Signal Pulse Response vs Load



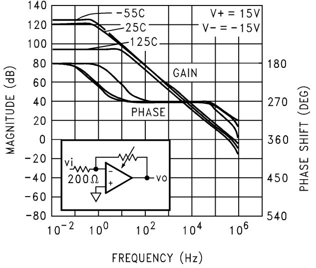
### Op Amp Voltage Noise vs Frequency



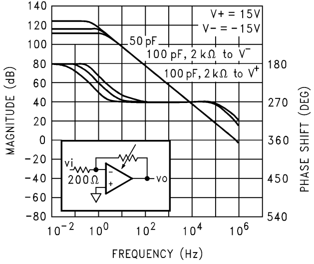
### Op Amp Current Noise vs Frequency



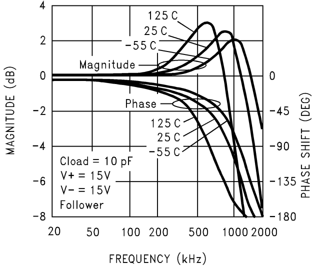
### Small-Signal Voltage Gain vs Frequency and Temperature



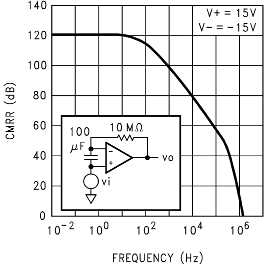
### Small-Signal Voltage Gain vs Frequency and Load



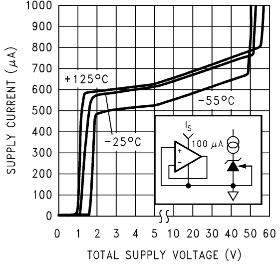
### Follower Small-Signal Frequency Response



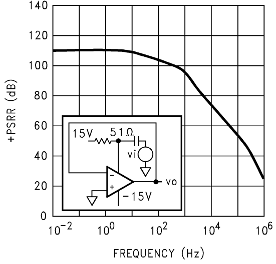
### Common-Mode Input Voltage Rejection Ratio



### Power Supply Current vs Power Supply Voltage



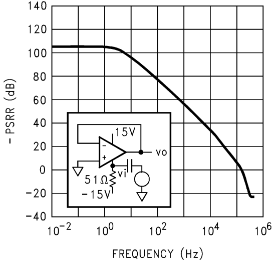
### Positive Power Supply Voltage Rejection Ratio



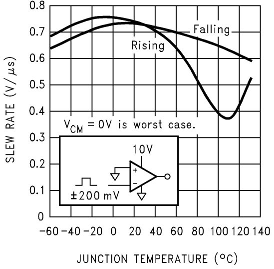
## Typical Performance Characteristics (Op Amps) (continued)

$V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25°C$, unless otherwise noted

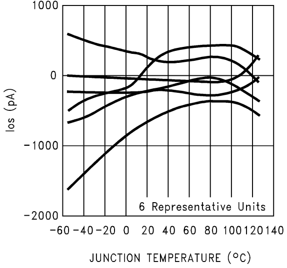
**Negative Power Supply Voltage Rejection Ratio**



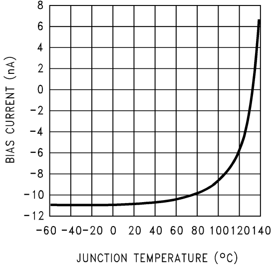
**Slew Rate vs Temperature**



**Input Offset Current vs Junction Temperature**

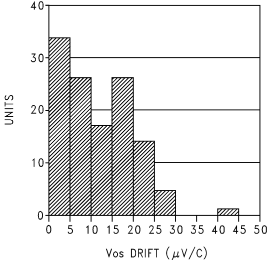


**Input Bias Current vs Junction Temperature**

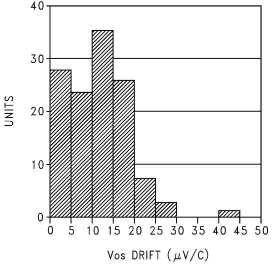


# Typical Performance Distributions

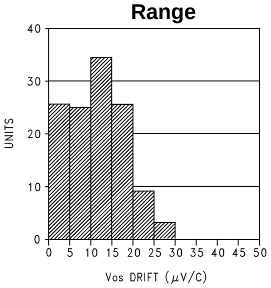
**Average $V_{OS}$ Drift Military Temperature Range**



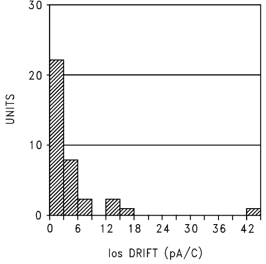
**Average $V_{OS}$ Drift Industrial Temperature Range**



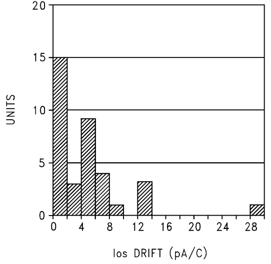
**Average $V_{OS}$ Drift Commercial Temperature Range**



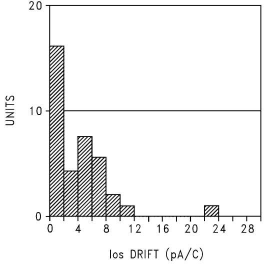
**Average $I_{OS}$ Drift Military Temperature Range**



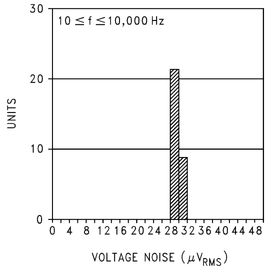
**Average $I_{OS}$ Drift Industrial Temperature Range**



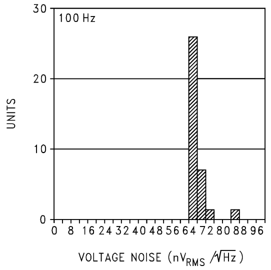
**Average $I_{OS}$ Drift Commercial Temperature Range**



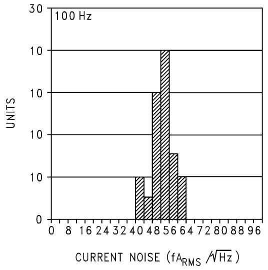
**Voltage Reference Broad-Band Noise Distribution**



**Op Amp Voltage Noise Distribution**



**Op Amp Current Noise Distribution**



## Application Information

### VOLTAGE REFERENCE

#### *Reference Biasing*

The voltage reference is of a shunt regulator topology that models as a simple zener diode. With current $I_r$ flowing in the 'forward' direction there is the familiar diode transfer function. $I_r$ flowing in the reverse direction forces the reference voltage to be developed from cathode to anode. The applied voltage to the cathode may range from a diode drop below $V^-$ to the reference voltage or to the avalanche voltage of the parallel protection diode, nominally 7V. A 6.3V reference with V+ = 3V is allowed.

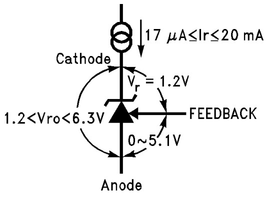


**Figure 1. Voltages Associated with Reference (Current Source $I_r$ is External)**

The reference equivalent circuit reveals how $V_r$ is held at the constant 1.2V by feedback, and how the FEEDBACK pin passes little current.

To generate the required reverse current, typically a resistor is connected from a supply voltage higher than the reference voltage. Varying that voltage, and so varying $I_r$, has small effect with the equivalent series resistance of less than an ohm at the higher currents. Alternatively, an active current source, such as the LM134 series, may generate $I_r$.

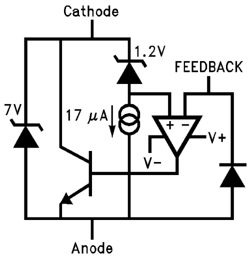


**Figure 2. Reference Equivalent Circuit**

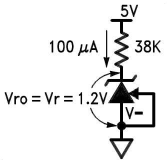


**Figure 3. 1.2V Reference**

Capacitors in parallel with the reference are allowed. See the Reference AC Stability Range curve for capacitance values—from 20 μA to 3 mA any capacitor value is stable. With the reference's wide stability range with resistive and capacitive loads, a wide range of RC filter values will perform noise filtering.

### *Adjustable Reference*

The FEEDBACK pin allows the reference output voltage, $V_{ro}$, to vary from 1.24V to 6.3V. The reference attempts to hold $V_r$ at 1.24V. If $V_r$ is above 1.24V, the reference will conduct current from Cathode to Anode; FEEDBACK current always remains low. If FEEDBACK is connected to Anode, then $V_{ro} = V_r = 1.24V$. For higher voltages FEEDBACK is held at a constant voltage above Anode—say 3.76V for $V_{ro} = 5V$. Connecting a resistor across the constant $V_r$ generates a current $I=R1/V_r$ flowing from Cathode into FEEDBACK node. A Thevenin equivalent 3.76V is generated from FEEDBACK to Anode with R2=3.76/I. Keep I greater than one thousand times larger than FEEDBACK bias current for <0.1% error—I≥32 μA for the military grade over the military temperature range (I≥5.5 μA for a 1% untrimmed error for a commercial part.)

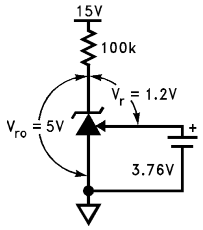
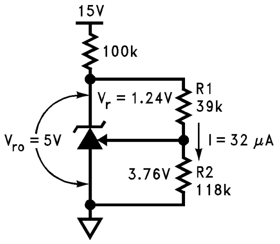


**Figure 4. Thevenin Equivalent of Reference with 5V Output**



R1 = Vr/I = 1.24/32μ = 39k

R2 = R1 {(Vro/Vr) − 1} = 39k {(5/1.24) − 1)} = 118k

**Figure 5. Resistors R1 and R2 Program Reference Output Voltage to be 5V**

Understanding that $V_r$ is fixed and that voltage sources, resistors, and capacitors may be tied to the FEEDBACK pin, a range of $V_r$ temperature coefficients may be synthesized.

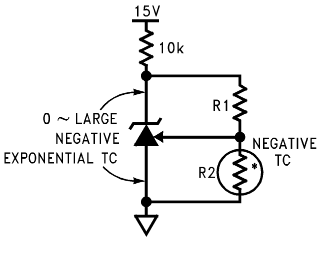


**Figure 6. Output Voltage has Negative Temperature Coefficient (TC) if R2 has Negative TC**

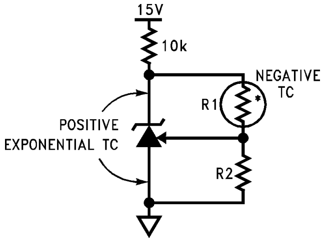


Figure 7. Output Voltage has Positive TC if R1 has Negative TC

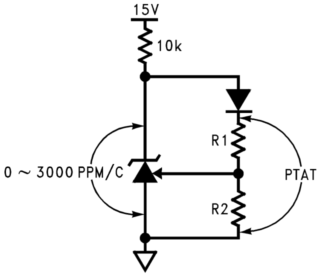
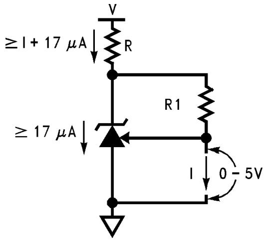


Figure 8. Diode in Series with R1 Causes Voltage Across R1 and R2 to be Proportional to Absolute Temperature (PTAT)

Connecting a resistor across Cathode-to-FEEDBACK creates a 0 TC current source, but a range of TCs may be synthesized.



I = Vr/R1 = 1.24/R1

Figure 9. Current Source is Programmed by R1

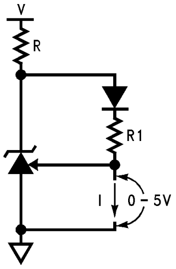


Figure 10. Proportional-to-Absolute-Temperature Current Source

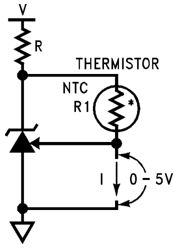


**Figure 11. Negative −TC Current Source**

### *Hysteresis*

The reference voltage depends, slightly, on the thermal history of the die. Competitive micro-power products vary—always check the data sheet for any given device. Do not assume that no specification means no hysteresis.

## OPERATIONAL AMPLIFIER

The amp or the reference may be biased in any way with no effect on the other, except when a substrate diode conducts (see Guaranteed Electrical Characteristics Note 1). The amp may have inputs outside the common-mode range, may be operated as a comparator, or have all terminals floating with no effect on the reference (tying inverting input to output and non-inverting input to $V^-$ on unused amp is preferred). Choosing operating points that cause oscillation, such as driving too large a capacitive load, is best avoided.

### *Op Amp Output Stage*

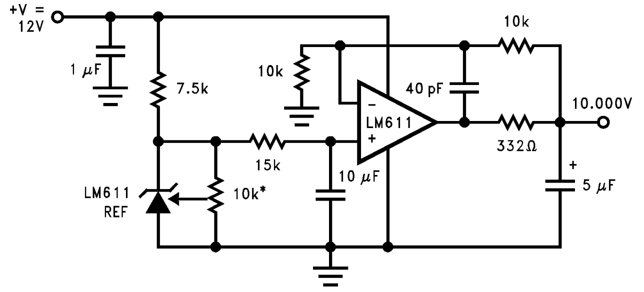
The op amp, like the LM124 series, has a flexible and relatively wide-swing output stage. There are simple rules to optimize output swing, reduce cross-over distortion, and optimize capacitive drive capability:

1. Output Swing: Unloaded, the 42 μA pull-down will bring the output within 300 mV of $V^-$ over the military temperature range. If more than 42 μA is required, a resistor from output to $V^-$ will help. Swing across any load may be improved slightly if the load can be tied to $V^+$, at the cost of poorer sinking open-loop voltage gain.
2. Cross-over Distortion: The LM611 has lower cross-over distortion (a 1 $V_{BE}$ deadband versus 3 $V_{BE}$ for the LM124), and increased slew rate as shown in the characteristic curves. A resistor pull-up or pull-down will force class-A operation with only the PNP or NPN output transistor conducting, eliminating cross-over distortion.
3. Capacitive Drive: Limited by the output pole caused by the output resistance driving capacitive loads, a pull-down resistor conducting 1 mA or more reduces the output stage NPN $r_e$ until the output resistance is that of the current limit 25Ω. 200 pF may then be driven without oscillation.

### *Op Amp Input Stage*

The lateral PNP input transistors, unlike those of most op amps, have $BV_{EBO}$ equal to the absolute maximum supply voltage. Also, they have no diode clamps to the positive supply nor across the inputs. These features make the inputs look like high impedances to input sources producing large differential and common-mode voltages.

## Typical Applications



*10k must be low
t.c. trim pot.

**Figure 12. Ultra Low Noise 10.00V Reference. Total Output Noise is Typically 14 µ$V_{RMS}$. Adjust the 10k pot for 10.000V.**

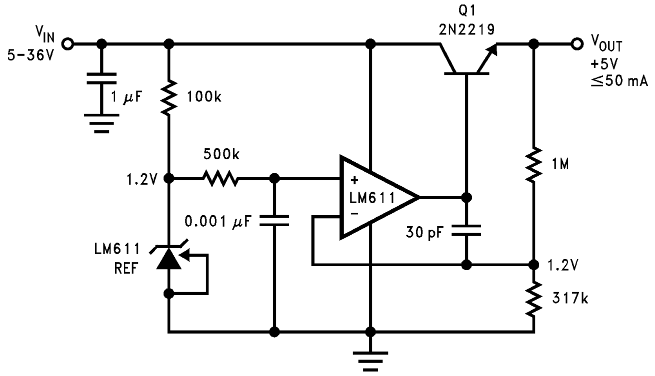
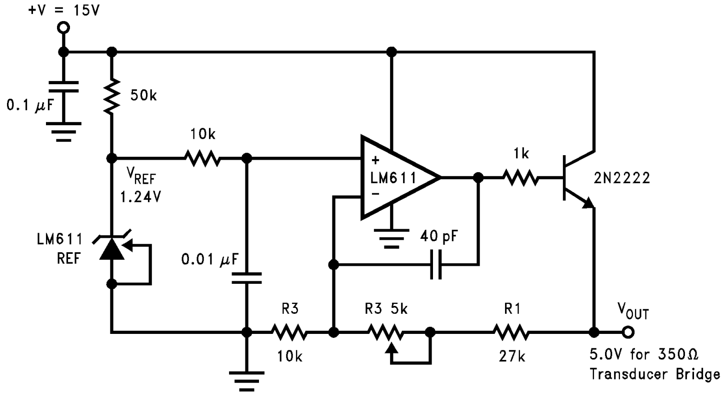


**Figure 13. Simple Low Quiescent Drain Voltage Regulator. Total Supply Current is approximately 320 µA when $V_{IN}$ = 5V, and output has no load.**



$V_{OUT}$ = (R1/R2 + 1) $V_{REF}$.
R1, R2 should be 1% metal film.
R3 should be low t.c. trim pot.

**Figure 14. Slow Rise-Time Upon Power-Up, Adjustable Transducer Bridge Driver. Rise-time is approximately 0.5 ms.**

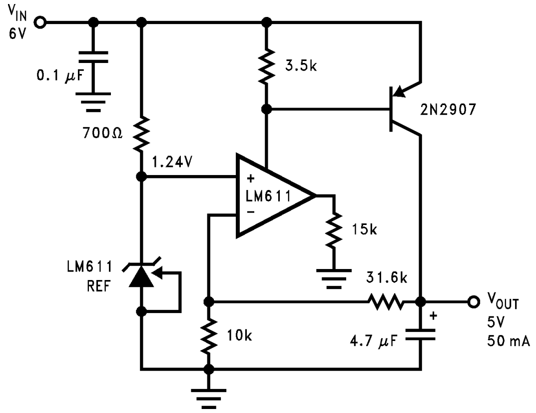


**Figure 15. Low Drop-Out Voltage Regulator Circuit. Drop out voltage is typically 0.2V.**

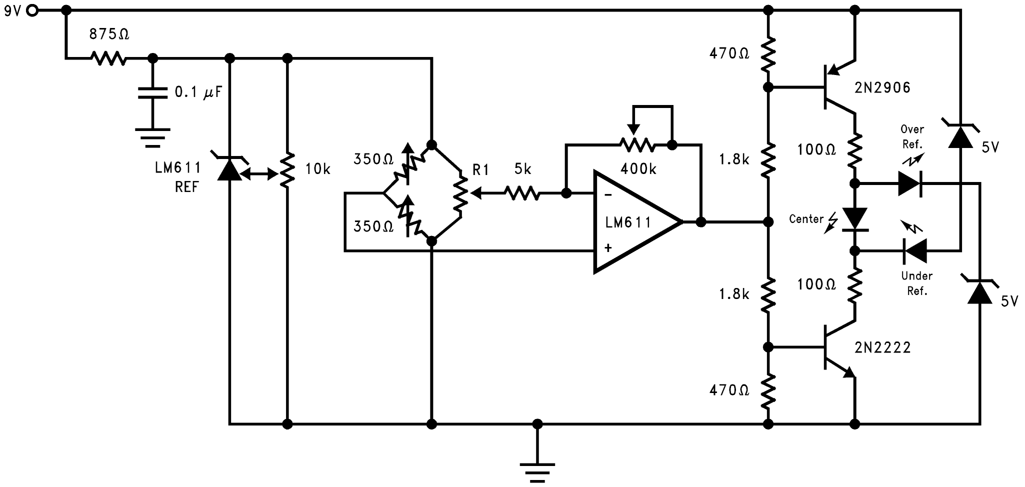


**Figure 16. Nulling Bridge Detection System. Adjust sensitivity via 400 kΩ pot. Null offset with R1, and bridge drive with the 10k pot.**

## Simplified Schematic Diagrams

**Figure 17. Op Amp**

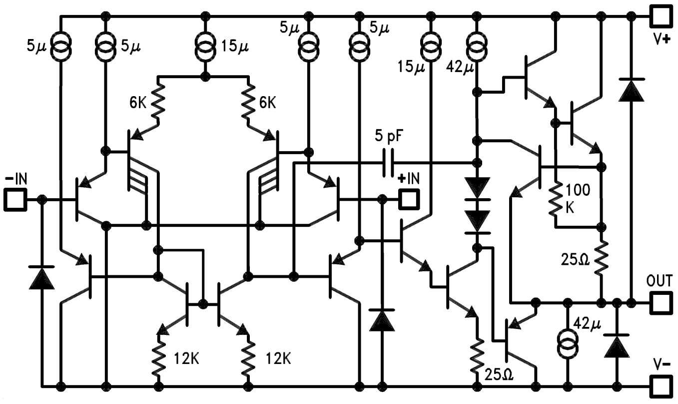


**Figure 18. Reference**

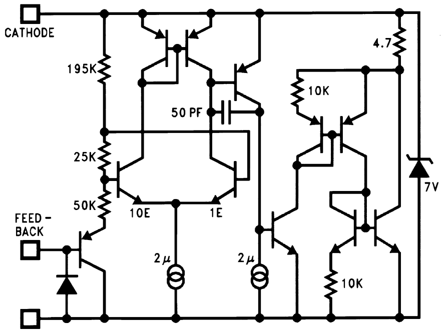
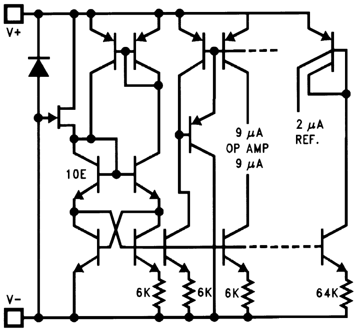


**Figure 19. Bias**



## PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish | MSL Peak Temp (3) | Op Temp (°C) | Top-Side Markings (4) | Samples |
|---|---|---|---|---|---|---|---|---|---|---|---|
| LM611CM | ACTIVE | SOIC | D | 14 | 55 | TBD | CU SNPB | Level-1-235C-UNLIM | 0 to 70 | LM611CM | Samples |
| LM611CM/NOPB | ACTIVE | SOIC | D | 14 | 55 | Green (RoHS & no Sb/Br) | CU SN | Level-1-260C-UNLIM | 0 to 70 | LM611CM | Samples |
| LM611CMX | ACTIVE | SOIC | D | 14 | 2500 | TBD | CU SNPB | Level-1-235C-UNLIM | 0 to 70 | LM611CM | Samples |
| LM611CMX/NOPB | ACTIVE | SOIC | D | 14 | 2500 | Green (RoHS & no Sb/Br) | CU SN | Level-1-260C-UNLIM | 0 to 70 | LM611CM | Samples |
| LM611IM | ACTIVE | SOIC | D | 14 | 55 | TBD | CU SNPB | Level-1-235C-UNLIM | -40 to 85 | LM611IM | Samples |
| LM611IM/NOPB | ACTIVE | SOIC | D | 14 | 55 | Green (RoHS & no Sb/Br) | CU SN | Level-1-260C-UNLIM | -40 to 85 | LM611IM | Samples |
| LM611IMX | ACTIVE | SOIC | D | 14 | 2500 | TBD | CU SNPB | Level-1-235C-UNLIM | -40 to 85 | LM611IM | Samples |
| LM611IMX/NOPB | ACTIVE | SOIC | D | 14 | 2500 | Green (RoHS & no Sb/Br) | CU SN | Level-1-260C-UNLIM | -40 to 85 | LM611IM | Samples |

(1) The marketing status values are defined as follows:
**ACTIVE:** Product device recommended for new designs.
**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.
**OBSOLETE:** TI has discontinued the production of the device.

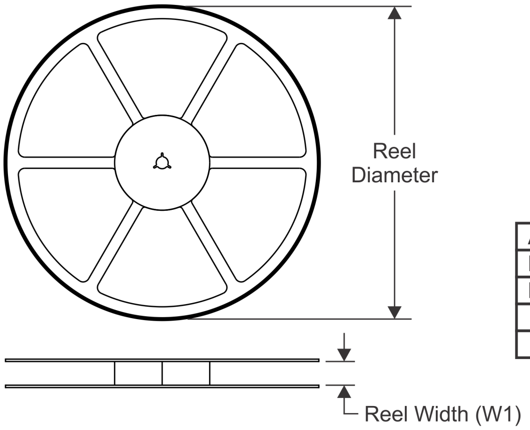
(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
**TBD:** The Pb-Free/Green conversion plan has not been defined.
**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

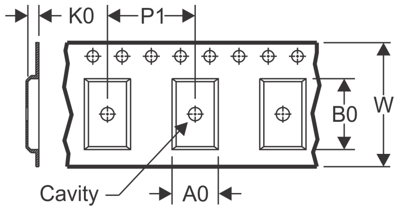
(4) Only one of markings shown within the brackets will appear on the physical device.

## TAPE AND REEL INFORMATION

### REEL DIMENSIONS

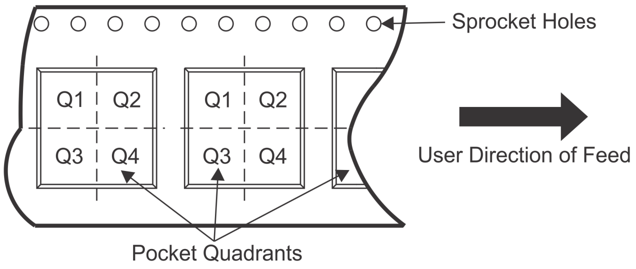


### TAPE DIMENSIONS



| | |
|---|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

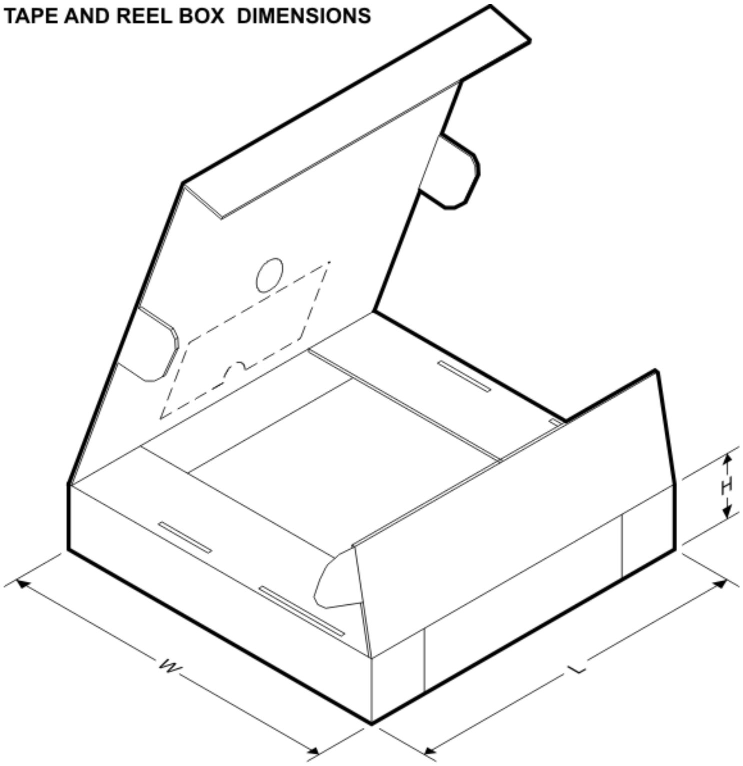
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| LM611CMX | SOIC | D | 14 | 2500 | 330.0 | 16.4 | 6.5 | 9.35 | 2.3 | 8.0 | 16.0 | Q1 |
| LM611CMX/NOPB | SOIC | D | 14 | 2500 | 330.0 | 16.4 | 6.5 | 9.35 | 2.3 | 8.0 | 16.0 | Q1 |
| LM611IMX | SOIC | D | 14 | 2500 | 330.0 | 16.4 | 6.5 | 9.35 | 2.3 | 8.0 | 16.0 | Q1 |
| LM611IMX/NOPB | SOIC | D | 14 | 2500 | 330.0 | 16.4 | 6.5 | 9.35 | 2.3 | 8.0 | 16.0 | Q1 |

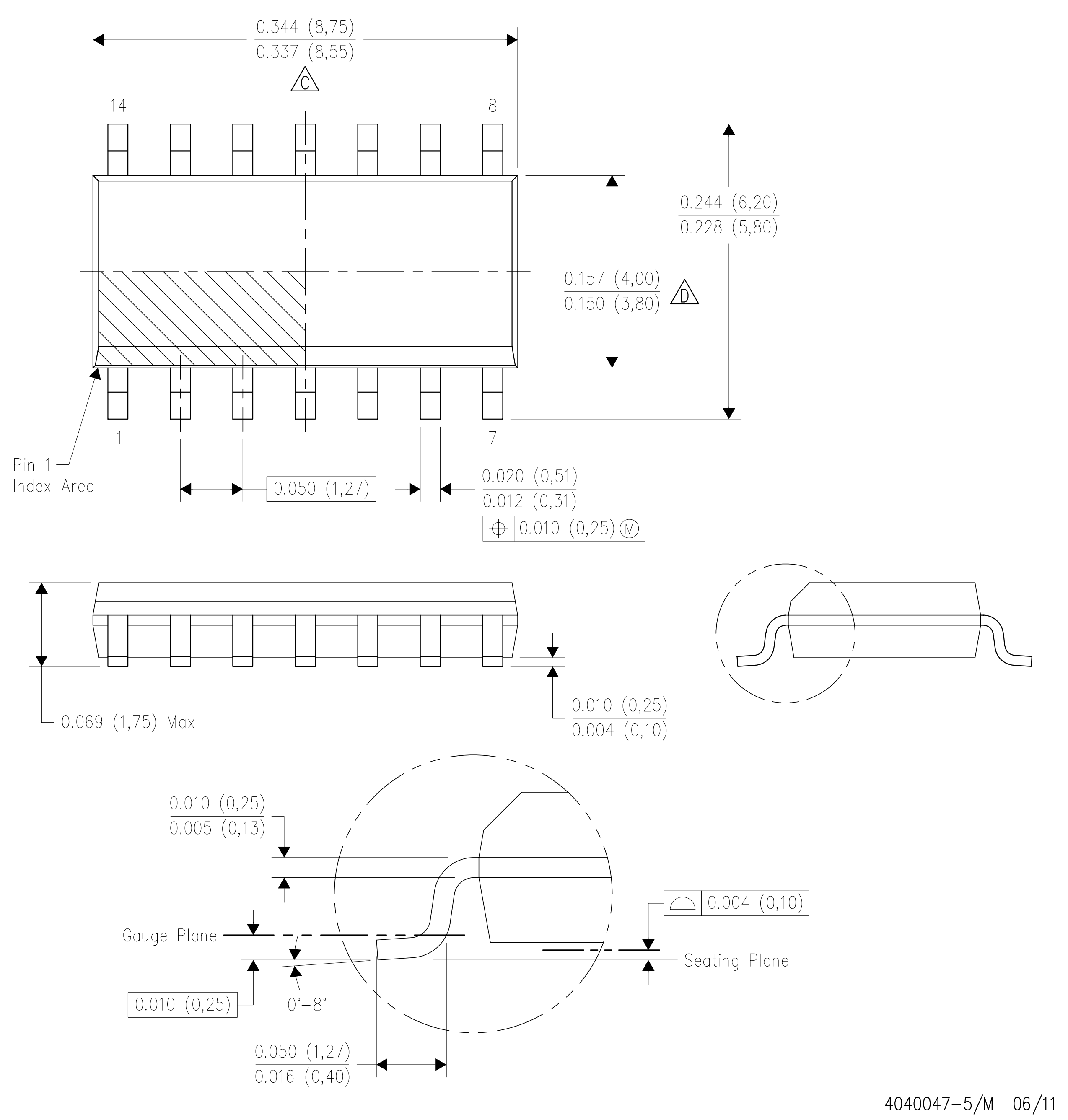
## TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|---|---|---|---|---|---|---|
| LM611CMX | SOIC | D | 14 | 2500 | 349.0 | 337.0 | 45.0 |
| LM611CMX/NOPB | SOIC | D | 14 | 2500 | 349.0 | 337.0 | 45.0 |
| LM611IMX | SOIC | D | 14 | 2500 | 349.0 | 337.0 | 45.0 |
| LM611IMX/NOPB | SOIC | D | 14 | 2500 | 349.0 | 337.0 | 45.0 |

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040047-5/M 06/11

NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

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